

Schottky barrier diodes

BYV10 series

FEATURES

- Low switching losses
- Fast recovery time
- Guard ring protected
- Hermetically sealed leaded glass package.

DESCRIPTION

The BYV10-20 to BYV10-40 types are Schottky barrier diodes fabricated in planar technology, and encapsulated in SOD81 hermetically sealed glass packages incorporating Implotec^{TM(1)} technology.

(1) Implotec is a trademark of Philips.

APPLICATIONS

- Low power, switched-mode power supplies
- Rectifying
- Polarity protection.

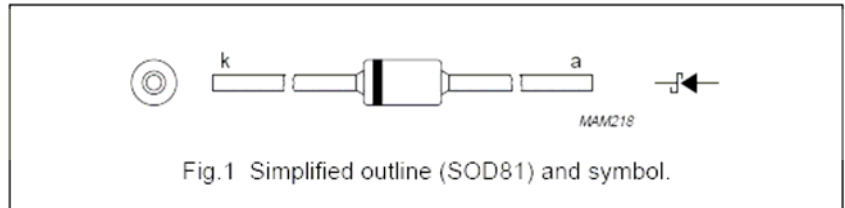


Fig.1 Simplified outline (SOD81) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{RRM}	repetitive peak reverse voltage 可重复反向恢复电压				
	BYV10-20		–	20	V
	BYV10-30		–	30	V
	BYV10-40		–	40	V
I _{F(AV)}	average forward current	note 1	–	1	A
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	125	°C

ELECTRICAL CHARACTERISTICS

T_{amb} = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _F	forward voltage 正向压降	I _F = 0.1 A	–	–	390	mV
		I _F = 1 A	–	–	550	mV
		I _F = 3 A	–	–	850	mV
I _R	reverse current	V _R = V _{RRMmax} ; note 1	–	–	1	mA
C _d	diode capacitance	V _R = 0 V; f = 1 MHz	–	220	–	pF

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{thj-a}	thermal resistance from junction to ambient	note 1	100	K/W

